

Correlation between structural change and electrical transport properties of indium nitride under high pressure

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Supplementary Information for Publication

Table S1. Values of E_g and dE_g/dP for the different candidate phases of InN and the phase transition pressures. B1, B2, and B3 represent the rocksalt, wurtzite, and zinc-blende phase of InN, respectively.

Compound	Phase	Pressure (GPa)	E_g (eV)		dE_g/dP (meV/GPa)	
			Present work	other calculation	Present work	other calculation
	B3	0		0.0 ^{a,b,c}		19.94 ^c
				0.02 ^d		16.0 ^d
				0.5813 ^e		
				0.753 ^e , 0.75 ^f		34.0 ^c
	B2	0	0.08		16.5	
				-0.354 ^g , -0.18 ^h ,		23.4 ^g
				-0.160 ⁱ , -0.118 ^g		
				0.00 ⁱ , 0.03 ^h		
						21.0 ^j
				0.26 ^d , 0.694 ^g		33.0 ^d , 31.0 ^g
				0.711 ^g		26.1 ^g
				0.772 ⁱ , 0.805 ^g		34.0 ^g
InN	B1	0		0.0573 ^e , 0.22 ^a , 0.372 ^k		9.4 ^e
				0.6153 ^e		64.7 ^e
				0.6887 ^e		
				0.7438 ^e		44.7 ^e
	B3-B1	10.0		0.00 ^a , 0.081 ^l		
		10.5 ^k				
		11.84 ^m				
	B2-B1	10.0	0.28		33.0	
		10.2		0.4 ⁿ		18.0 ⁿ
		10.86 ^m				

		11.1		0.75 ^k		24.9 ^k
		13.0		0.1803 ^e , 1.3249 ^e , 1.4571 ^e		
		16.0				22.0 ^o
		21.6		1.66 ^d		41.0 ^d

^aPlane wave self-consistent method with GGA-PBE (Ref. 1).

^bFP-LAPW method with MBJLDA (modified Becke-Johnson exchange potential+LDA) (Ref. 2).

^cFPLAPW method with LDA (Ref. 3).

^dSelf-consistent LMTO method with LDA-ASA (Ref. 4).

^ePAW method with HSE06, GW, and GGA, respectively (Ref. 5).

^fPW-PP method with LDA+ HGH (Ref. 6).

^gPAW method with PBE, HSE06, G₀W₀(HSE06), scGW₀, G₀W₀(PBE), and GGA, respectively (Ref. 7).

^hPAW method with LDA+U (Ref. 8).

ⁱPAW method with GGA, GGA+U, and HSE, respectively (Ref. 9).

^jLAPW method with LDA (Ref. 10).

^kTroullier-Martins pseudopotentials, DFT-LDA (Ref. 11).

^lFP-LAPW method with GGA-EV (Ref. 12).

^mDFT with both LDA and GGA (Ref. 13).

ⁿPlane wave pseudopotential with LDA (Ref. 14).

^oPlane wave basis and with pseudopotentials, LDA+U (Ref. 15).

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